Supporting information

Broadband emitting phosphor Sr₆Sc₂Al₄O₁₅:Cr³⁺ for near-infrared LEDs

Jinyi Wang, Xudong Wang, Chenjie Zhang, Xinyu Zhang, Tianliang Zhou^{*} *and Rong-Jun Xie*^{*}

Fujian Key Laboratory of Surface and Interface Engineering for High Performance Materials, College of Materials, Xiamen University, Xiamen 361005, P. R. China

Corresponding Authors

*E-mail: bible2@163.com (T.Z.). *E-mail: rjxie@xmu.edu.cn (R.-J.X.).

Phosphor	$\lambda_{ex}(nm)$	$\lambda_{em}(nm)$	Spectral profile	Ref.
MgGeO ₃ :Pr ³⁺	254	625	Multi-narrowband	1
$K_3LuSi_2O_7{:}Eu^{2+}$	460	740	Broadband	2
$Sr_3Li_4Si_2N_6{:}Eu^{2+}$	450	800	Broadband	3
$Lu_3Sc_2Ga_3O_{12}{:}Yb^{3+}$	850	976	Multi-narrowband	4
$La_3Si_6N_{11}{:}Yb^{3+}$	365	983	Narrowband	5
LaSrGaO ₄ :Nd ³⁺	808	1076	Multi-narrowband	6
$Y_2Ti_2O_7{:}Bi^{3+}$	391	744	Broadband	7
$Cs_2ZnCl_4:Sb^{3+}$	316	745	Broadband	8
FAPbI ₃ :Sn ²⁺	510	784	Narrowband	9
MgAl ₂ O ₄ :Mn ⁴⁺	440	651	Broadband	10
NaAlP ₂ O ₇ :Cr ³⁺	450	790	Broadband	11
MgAl ₂ O ₄ :Mn ²⁺	450	825	Broadband	12
CaMgGe ₂ O ₆ :Cr ³⁺	450	845	Broadband	13
CaMgSi ₂ O ₆ :Cr ³⁺	455	845	Broadband	14
LiGaP ₂ O ₇ :Cr ³⁺	452	846	Broadband	15
NaInP ₂ O ₇ :Cr ³⁺	460	870	Broadband	16
LiInGe ₂ O ₆ :Cr ³⁺	460	880	Broadband	17
Sr ₂ InSbO ₆ :Fe ³⁺	340	885	Broadband	18
NaScGe ₂ O ₆ :Cr ³⁺	490	895	Broadband	19
CaScAlSiO ₆ :Cr ³⁺	460	950	Broadband	20
ZnGa ₂ O ₄ :Ni ²⁺	260	1240	Broadband	21

Table S1. Excitation and emission peak wavelengths of some NIR phosphors.

Table S2. Crystallographic data of SSA: xCr^{3+} (x = 0.008, 0.08).

Formula	SSA:0.008Cr ³⁺	SSA:0.08Cr ³⁺
Crystal system	monoclinic	monoclinic
Space group	C 2	C 2
a (Å)	17.2395	17.2370
b (Å)	5.6304	5.6293
c (Å)	7.5588	7.5549
α, β, γ (deg.)	90, 91.28, 90	90, 91.25, 90
Rwp (%)	3.62	3.72
Rp (%)	2.81	2.87
χ^2	1.64	1.76

Table S3. Atomic coordinates and isotropic displacement parameters of SSA.

Atom	Х	У	Z	Occupancy
Sc1	0.3448(6)	0.4815(3)	0.7557(3)	1
Sr1	0.1719(6)	0.4850(7)	0.5027(1)	1
Sr2	0.1626(5)	0.4695(6)	0.9714(5)	1

Sr3	0	0.0137(8)	0	0.5
Sr4	0	0.0610(4)	0.5	0.5
Al1	0.3115(7)	0.4793(8)	0.2457(6)	1
Al2	0.0165(3)	0.5065(5)	0.2249(5)	1

Table S4. Atomic coordinates and isotropic displacement parameters of SSA:0.008Cr³⁺.

Atom	Х	у	Z	Occupancy
Sc1	0.3446(4)	0.5098(3)	0.7546(9)	0.996
Cr1	0.3446(4)	0.5098(3)	0.7546(9)	0.004
Sr1	0.1717(7)	0.5044(1)	0.5000(5)	1
Sr2	0.1618(4)	0.4866(2)	0.9704(5)	1
Sr3	0	0.0311(4)	0	0.5
Sr4	0	0.0871(1)	0.5	0.5
Al1	0.3112(6)	0.4862(2)	0.2434(9)	1
Al2	0.0153(4)	0.5350(9)	0.2273(7)	1

Table S5. Atomic coordinates and isotropic displacement parameters of SSA:0.08Cr³⁺.

Atom	Х	У	Z	Occupancy
Sc1	0.3441(5)	0.5069(3)	0.7561(6)	0.96
Cr1	0.3441(5)	0.5069(3)	0.7561(6)	0.04
Sr1	0.1713(6)	0.5056(6)	0.5017(1)	1
Sr2	0.1624(4)	0.4904(8)	0.9709(2)	1
Sr3	0	0.0329(8)	0	0.5
Sr4	0	0.0857(9)	0.5	0.5
Al1	0.3114(5)	0.4879(1)	0.2422(7)	1
Al2	0.0164(1)	0.5370(5)	0.2299(5)	1

Table S6. ESR resonance signals of some Cr³⁺-doped NIR phosphors.

Dhaanhana	Resonance	Def	
Phosphors	Isolated Cr ³⁺ ions	Cr ³⁺ -Cr ³⁺ pairs	Kel.
LiScGeO ₄	<i>g</i> = 4.22	<i>g</i> = 1.97	22
$Gd_{2.4}Lu_{0.6}Ga_4AlO_{12}$	<i>g</i> = 4.22	<i>g</i> = 1.97	23
Ga ₄ GeO ₈	g = 4.89	<i>g</i> = 2.02	24
La ₂ MgHfO ₆	/	<i>g</i> = 1.99	25
La ₂ MgZrO ₆	<i>g</i> = 4.22	<i>g</i> = 1.97	26
GdAl ₃ (BO ₃) ₄	/	<i>g</i> = 1.98	27
$La_{3}Ga_{5.5}Nb_{0.5}O_{14}$	g = 3.80	<i>g</i> = 1.94	28
LiScGeO ₄	g = 3.878	g = 2.007	29
$Lu_2CaMg_2Si_3O_{12}\\$	<i>g</i> = 4.32	<i>g</i> = 1.98	30

Table S6 lists the g value of some Cr doped NIR phosphors. The average g value was calculated

to be 4.22 ($\sigma^2 = 0.11$) and 1.98 ($\sigma^2 = 4.81*10^{-4}$) (representing the isolated Cr³⁺ ions and Cr³⁺-Cr³⁺ pairs, respectively). Apparently, the *g* values of SSA:0.008Cr³⁺ are close to the average calculated *g* values.

Phosphors	Binding energy (eV)	Ref.
SnO ₂	Cr-2p _{1/2} (586.7); Cr-2p _{3/2} (577.0)	31
$Sr_2P_2O_7$	Cr-2p _{3/2} (577.0)	32
La ₂ MgHfO ₆	Cr-2p _{1/2} (586.3); Cr-2p _{3/2} (576.3)	25
$K_2Ga_2Sn_6O_{16}$	Cr-2p _{3/2} (576.01)	33
Mg ₇ Ga ₂ GeO ₁₂	Cr-2p _{1/2} (582.5)	34
$CaLu_2Mg_2Si_3O_{12}\\$	Cr-2p _{3/2} (577.0)	35
Ga ₄ GeO ₈	Cr-2p _{3/2} (576.0)	24
$Gd_{2.4}Lu_{0.6}Ga_4AlO_{12}$	Cr-2p _{3/2} (576.4; 580.9)	23
LiScGeO ₄	Cr-2p _{1/2} (586.7)	22

Table S7. Binding energy of Cr^{3+} of some NIR phosphors.

Table S7 lists the binding energy of Cr^{3+} of some NIR phosphors. The average binding energy of Cr^{3+} was calculated to be 576.53 eV ($\sigma^2 = 0.1834$) (representing the Cr-2p_{3/2}). Apparently, the binding energy of Cr^{3+} in SSA:0.008Cr³⁺ is close to the average value.



Fig. S1. Photoluminescence and photoluminescence excitation spectra of SSA:0.2Ce³⁺.



Fig. S2. Decay curves of SSA:0.008Cr³⁺ monitored at different wavelengths (810 nm, 830 nm and 850 nm, respectively).



Fig. S3. Calculated band structure of $Sr_6Sc_2Al_4O_{15}$.

The calculation was performed via the density functional theory with the generalized gradientcorrected Perdew–Burke–Ernzerhof function. The kinetic energy cutoff and SCF tolerance were 340 eV and 10⁻⁵ eV/atom.



Fig. S4. Relationship between log(I/x) and log(x) of SSA: xCr^{3+} (x = 0-0.2).

Discussion:

The energy transfer and concentration quenching mechanism of phosphors are generally divided into three forms: exchange interaction, radiation recombination and electric multipolar interaction, which can be confirmed by calculating the R_c (the critical distance between adjacent Cr^{3+} ions) from the following formula:^{36, 37}

$$R_c = 2 \left(\frac{3V}{4\pi X_c N}\right)^{\frac{1}{3}} \tag{1}$$

Where V is the unite cell volume, N is the number of cations which can be occupied by Cr^{3+} in each unite cell, and X_c represents the doped concentration of Cr^{3+} ions. For SSA:0.008 Cr^{3+} , N = 15, V = 776.376921 Å, X_c = 0.004, after calculation, the R_c is 29.13 Å, far greater than the maximum distance of exchange interaction (5 Å). So the energy transfer mechanism between Cr^{3+} should be the multipolar interaction. In addition, the large R_c of 29.13 Å illustrates that fewer Cr^{3+} ions can be accommodated in the limited crystal cell space, leading to a low quenching concentration. And according to the theory of Dexter, the type of interaction can be determined by the following equation:

$$\frac{l}{x} = \frac{k}{1 + \beta(x)^3}$$
(2)

Where I is the emission intensity, x is the concentration of Cr^{3+} beyond the optimal doping

concentration, k and β are the constants of the same excitation conditions. θ represents the characteristic number of electric multipolarity. $\theta = 6$, 8 and 10 represents the dipole-dipole (d-d), dipole-quadrupole (d-q), and quadrupole-quadrupole (q-q) interactions, respectively. In order to obtain the value of θ , log(I/x) is plotted on the ordinate and log(x) is plotted on the abscissa, - $\theta/3$ is the slope of the linearly fitting line. Fig. S4 shows that the value of - $\theta/3$ is -1.51, so the value of θ is 4.53 (close to 6), which indicates that the quenching mechanism of Cr³⁺ is dipole-dipole (d-d) interaction in the SSA matrix.



Fig. S5. Tanabe-Sugano diagram for the d³ electronic configuration in an octahedral symmetry

For better understanding the interelectronic transitions that occur in d-orbitals, the Tanabe-Sugano diagram is illustrated in Fig. S5. According to the Tanabe–Sugano diagram, the relative energy position between the ${}^{4}T_{2}$ excited state and the ${}^{4}A_{2}$ ground state is strongly influenced by the crystal field strength (Dq/B). When Cr³⁺ is in an intermediate crystal field (Dq/B ~ 2.3), both ${}^{2}E \rightarrow {}^{4}A_{2}$ and ${}^{4}T_{2} \rightarrow {}^{4}A_{2}$ transitions can be observed in the emission spectra.³⁸ The value Dq/B of SSA:0.008Cr³⁺, monitored at 860 nm, is calculated to be 2.10, belonging to the intermediate crystal field.



Configurational coordinate diagram

Fig. S6. The schematic configuration coordinate diagram of SSA:0.008Cr³⁺ in an intermediate crystal field

For the intermediate crystal field, the ²E and ⁴T₂ states are leveled to one another. When Cr³⁺ ions were excited by the blue light, the electrons in the ⁴A₂ ground states transition to the ⁴T₁ excited states and relax afterward into the lowest excited state ²E and ⁴T₂ via non-radiative relaxation, then returning to the ground state through ²E→⁴A₂ and ⁴T₂→⁴A₂ transitions. When the temperature is rising, the electrons in the excited state ⁴T₂ will be excited to the intersection of ⁴T₂ and ⁴A₂ energy level, where the required energy ΔE is called activation energy. Then the electrons return to the ground state via non-radiative relaxation. The thermal stability depends on the offset (ΔR) between the two parabolas of the ground state and the lowest excited state, which is generally associated with the structural rigidity of host lattice.³⁹



Fig. S7. XRD of (a) NaScP₂O₇:0.01Cr³⁺; (b) KScP₂O₇:0.01Cr³⁺. Photoluminescence and photoluminescence excitation spectra of (c) NaScP₂O₇:0.01Cr³⁺; (d) KScP₂O₇:0.01Cr³⁺.

NaScP₂O₇:0.01Cr³⁺ and KScP₂O₇:0.01Cr³⁺ were synthesized via the conventional hightemperature solid-state reactions using chemical reagents of Na₂CO₃ (AR, Xi Long Scientific, Shantou, China), K₂CO₃ (AR, Sinopharm Chemical Reagent, Shanghai, China), Sc₂O₃ (4N, ZhongNuo Advanced Material Technology, Beijing, China), NH₄H₂PO₄ (AR, Sinopharm Chemical Reagent, Shanghai, China) and Cr₂O₃ (4N, Xi Long Scientific, Shantou, China) as starting materials. The starting materials were finely mixed with alcohol in an agate mortar for 25 mins. Then, the mixtures were loaded into alumina crucibles and fired in a tube furnace at 573 K for 2 h, and then at 1273 K for 6 h under the reducing atmosphere (N₂: H₂ = 9:1 in volume). As shown in Fig. S7 (a-b), all of the NaScP₂O₇:0.01Cr³⁺ and KScP₂O₇:0.01Cr³⁺ peaks match well with the standard ICSD cards (ICSD#260594 and ICSD#132289), and no other impurities are detected, indicating that Cr³⁺ doping does not change the structure of the NaScP₂O₇:0.01Cr³⁺ show emission peaks of 928 and 867 nm as well as FWHM of 203 and 160 nm, respectively.

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